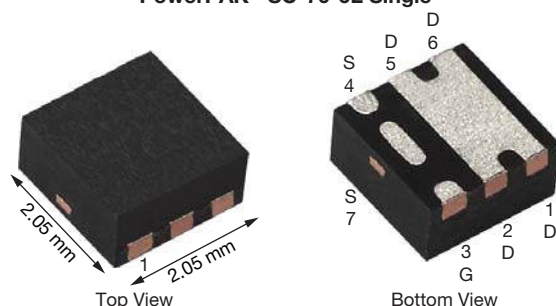


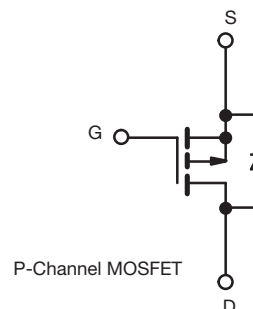
Automotive P-Channel 20 V (D-S) 175 °C MOSFET

PowerPAK® SC-70-6L Single

Marking Code: QBXXXX

PRODUCT SUMMARY	
V_{DS} (V)	-20
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.125
$R_{DS(on)}$ (Ω) at $V_{GS} = -2.5$ V	0.205
I_D (A)	-3.75
Configuration	Single
Package	PowerPAK SC-70

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified ^d
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE


P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-20	V
Gate-source voltage		V_{GS}	± 12	
Continuous drain current	$T_C = 25$ °C	I_D	-3.75	A
	$T_C = 125$ °C		-3.75	
Continuous source current (diode conduction) ^a		I_S	3.75	
Pulsed drain current ^b		I_{DM}	-12	
Single pulse avalanche current		I_{AS}	-8	
Single pulse avalanche energy		E_{AS}	3.2	mJ
Maximum power dissipation ^b	$T_C = 25$ °C	P_D	13.6	W
	$T_C = 125$ °C		4.5	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R_{thJA}	90	°C/W
Junction-to-case (drain)		R_{thJF}	11	

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- Parametric verification ongoing



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-20	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA		-0.6	-1.0	-1.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -20 V	-	-	-1	μA
		V _{GS} = 0 V	V _{DS} = -20 V, T _J = 125 °C	-	-	-50	
		V _{GS} = 0 V	V _{DS} = -20 V, T _J = 175 °C	-	-	-150	
On-state drain current ^a	I _{D(on)}	V _{GS} = -4.5 V	V _{DS} ≥ 5 V	-8	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -4.5 V	I _D = -2.4 A	-	0.085	0.125	Ω
		V _{GS} = -4.5 V	I _D = -2.4 A, T _J = 125 °C	-	-	0.175	
		V _{GS} = -4.5 V	I _D = -2.4 A, T _J = 175 °C	-	-	0.200	
		V _{GS} = -2.5 V	I _D = -1.8 A	-	0.160	0.205	
Forward transconductance ^b	g _{fs}	V _{DS} = -10 V, I _D = -2.4 A		-	6	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = -10 V, f = 1 MHz	-	265	330	pF
Output capacitance	C _{oss}			-	75	94	
Reverse transfer capacitance	C _{rss}			-	50	63	
Total gate charge ^c	Q _g	V _{GS} = -4.5 V	V _{DS} = -10 V, I _D = -2.4 A	-	3.4	5.5	nC
Gate-source charge ^c	Q _{gs}			-	0.6	-	
Gate-drain charge ^c	Q _{gd}			-	1.1	-	
Gate resistance	R _g	f = 1 MHz		4.8	9.6	14.4	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = -10 V, R _L = 5.21 Ω I _D ≅ -1.9 A, V _{GEN} = -4.5 V, R _g = 1 Ω		-	20	30	ns
Rise time ^c	t _r			-	18	27	
Turn-off delay time ^c	t _{d(off)}			-	19	28	
Fall time ^c	t _f			-	8	12	
Source-Drain Diode Ratings and Characteristics							
Pulsed current ^a	I _{SM}			-	-	-12.7	A
Forward voltage	V _{SD}	I _F = -2 A, V _{GS} = 0		-	-0.8	-1.2	V

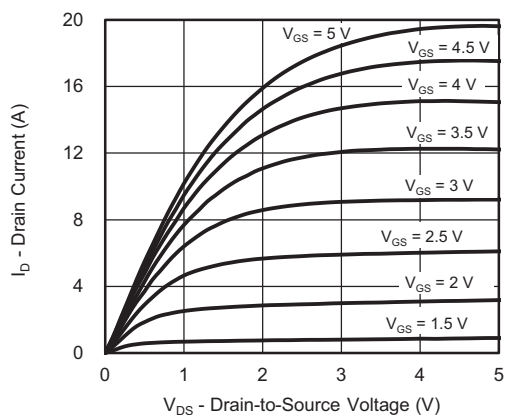
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

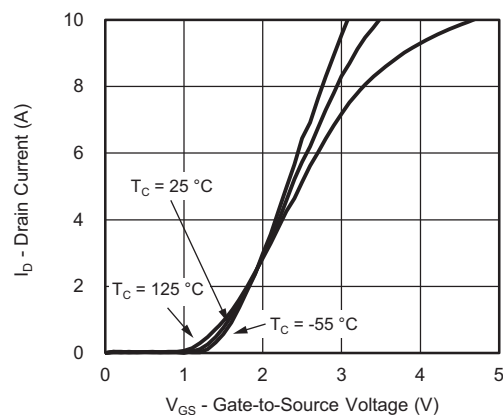
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



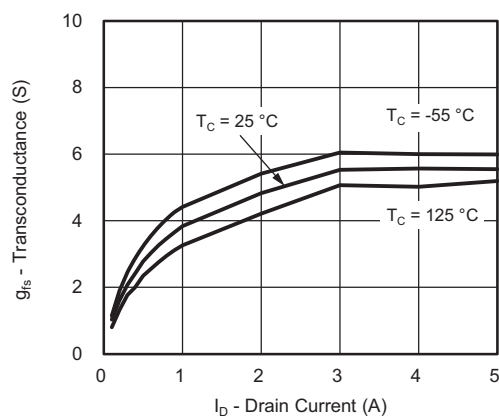
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



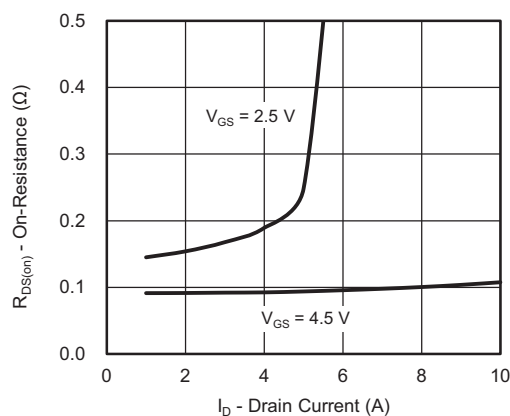
Output Characteristics



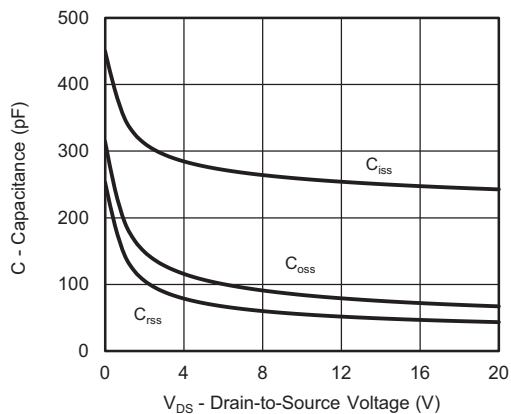
Transfer Characteristics



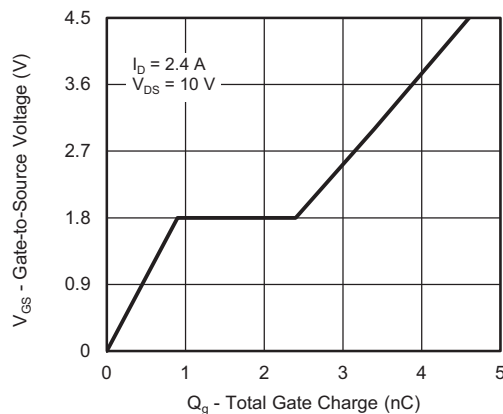
Transconductance



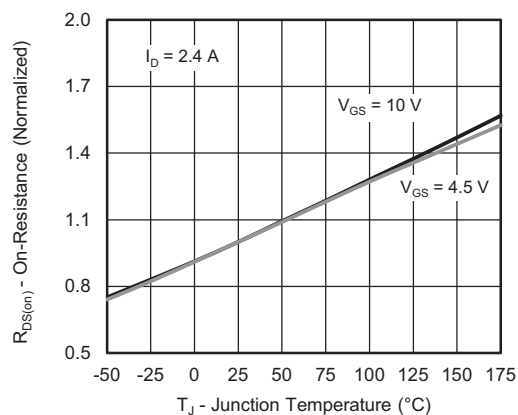
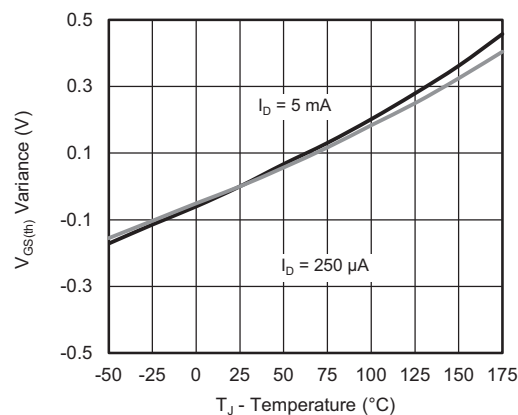
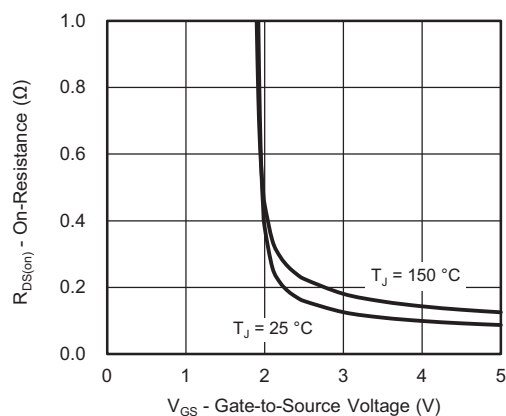
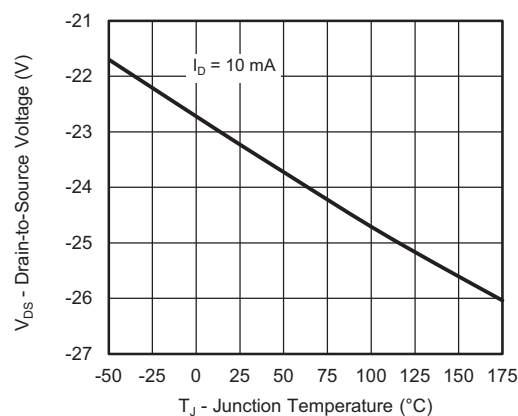
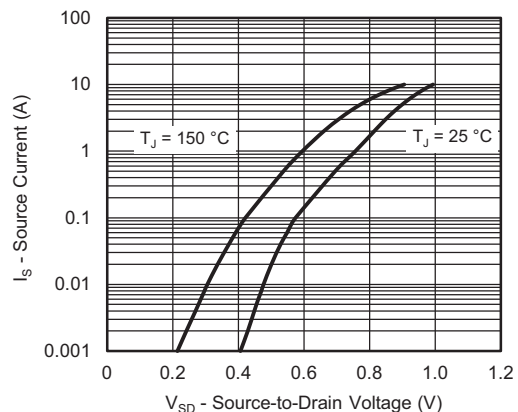
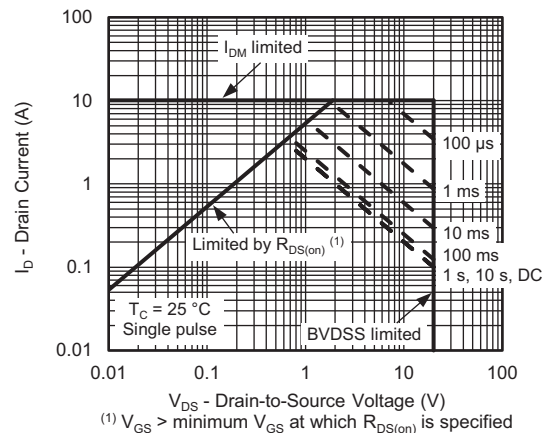
On-Resistance vs. Drain Current

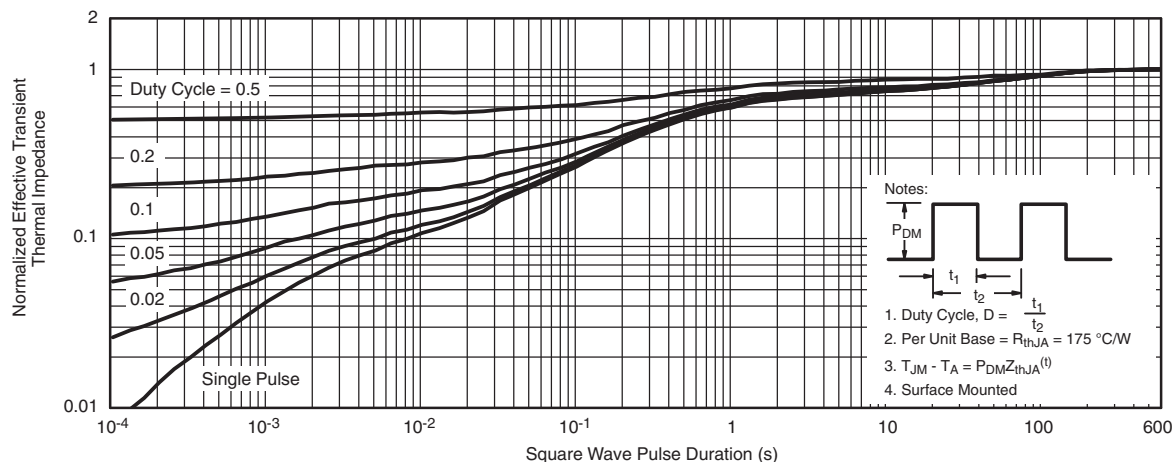
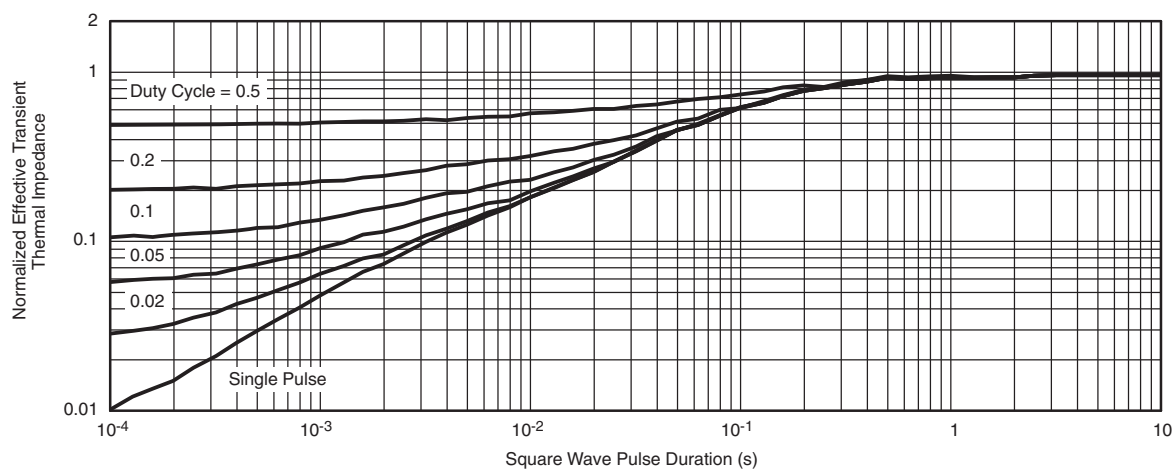


Capacitance



Gate Charge

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Threshold Voltage

On-Resistance vs. Gate-to-Source Voltage

Drain Source Breakdown vs. Junction Temperature

Source-Drain Diode Forward Voltage

Safe Operating Area

**THERMAL RATINGS** ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot****Note**

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^{\circ}\text{C}$)
- are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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